

2SB1219, 2SB1219A

Silicon PNP epitaxial planar type

For general amplification

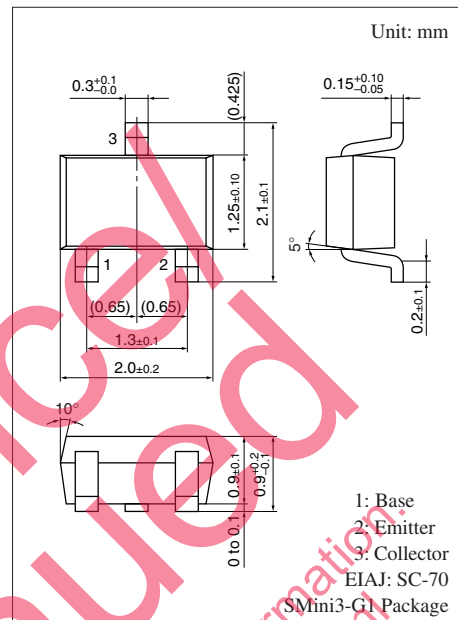
Complementary to 2SD1820 and 2SD1820A

■ Features

- Large collector current I_C
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	2SB1219	V_{CBO}	-30	V
	2SB1219A		-60	
Collector-emitter voltage (Base open)	2SB1219	V_{CEO}	-25	V
	2SB1219A		-50	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V	
Collector current	I_C	-500	mA	
Peak collector current	I_{CP}	-1	A	
Collector power dissipation	P_C	150	mW	
Junction temperature	T_j	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	



Marking Symbol:

- 2SB1219: C
- 2SB1219A: D

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	2SB1219	$I_C = -10 \mu\text{A}, I_E = 0$	-30			V
	2SB1219A		-60			
Collector-emitter voltage (Base open)	2SB1219	$I_C = -2 \text{ mA}, I_B = 0$	-25			V
	2SB1219A		-50			
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			-0.1	μA
Forward current transfer ratio *1	h_{FE1} *2	$V_{CE} = -10 \text{ V}, I_C = -150 \text{ mA}$	85		340	—
	h_{FE2}	$V_{CE} = -10 \text{ V}, I_C = -500 \text{ mA}$	40			
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = -300 \text{ mA}, I_B = -30 \text{ mA}$		-0.35	-0.60	V
Base-emitter saturation voltage *1	$V_{BE(sat)}$	$I_C = -300 \text{ mA}, I_B = -30 \text{ mA}$		-1.1	-1.5	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		6	15	pF

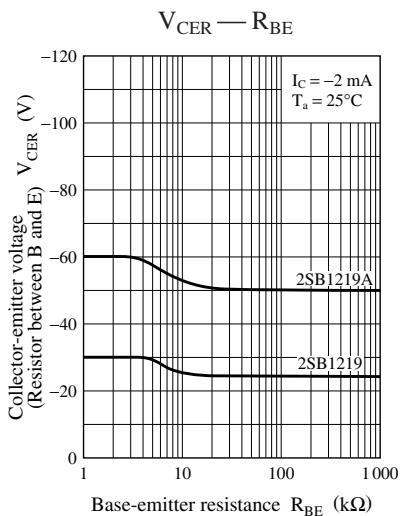
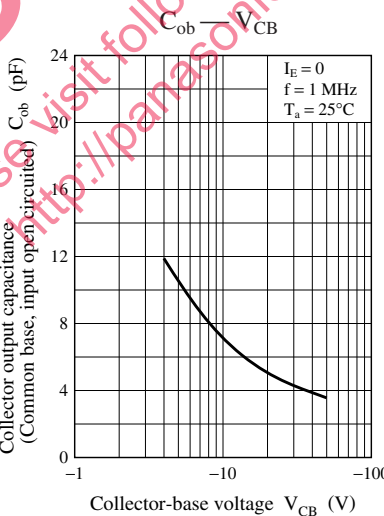
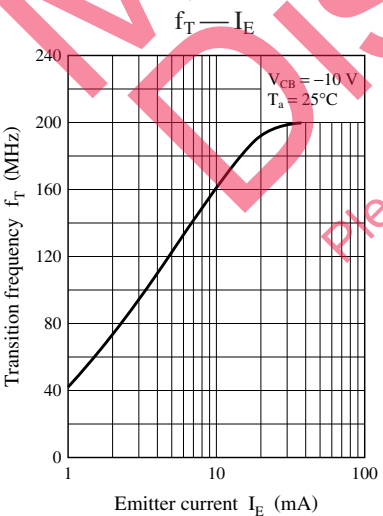
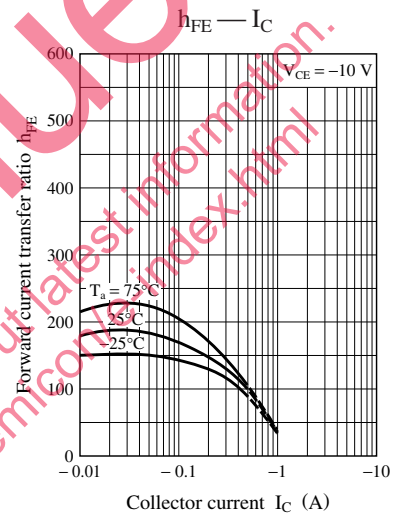
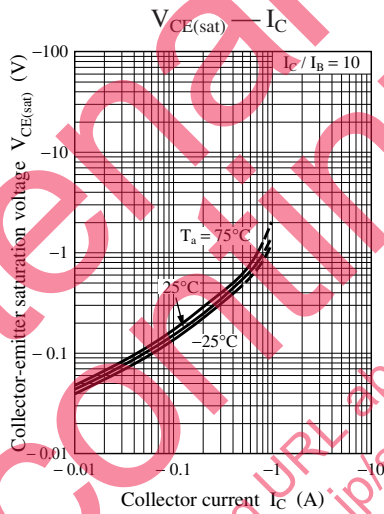
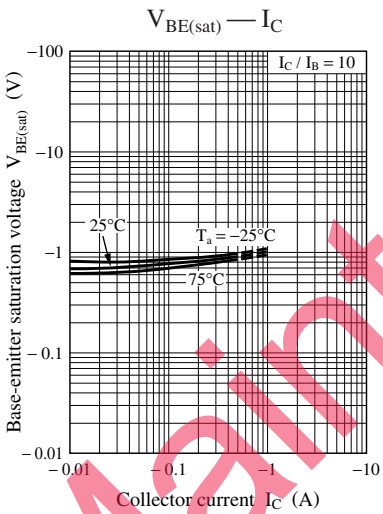
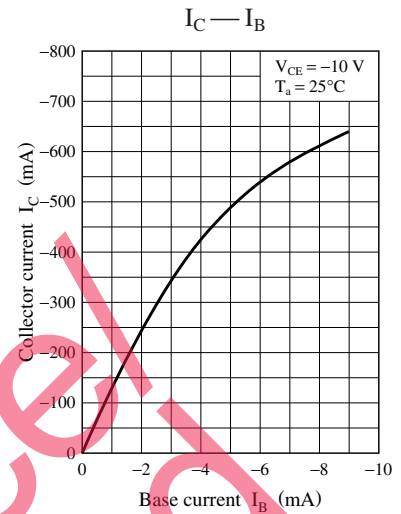
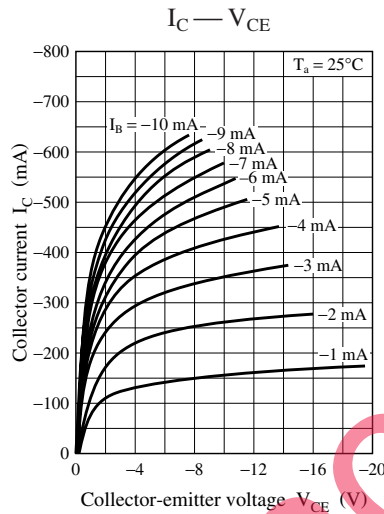
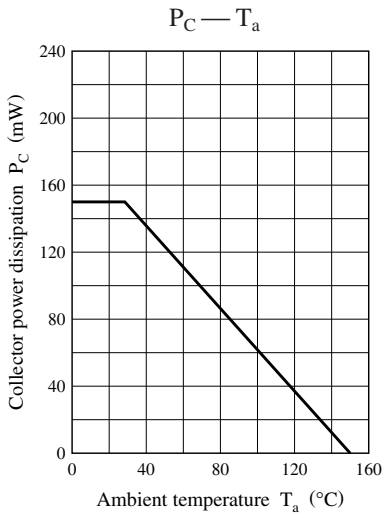
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

*2: Rank classification

Rank	Q	R	S	No-rank	
h_{FE1}	85 to 170	120 to 240	170 to 340	85 to 340	
Marking symbol	2SB1219	CQ	CR	CS	C
	2SB1219A	DQ	DR	DS	D

Note) Product of no-rank is not classified and have no marking symbol for rank.



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